



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

LL4148

LL-34 High Speed Switching Diode 高速开关二极管



■ Features 特点

Characteristic 特性参数	Symbol 符号	Value 额定值	Unit 单位
Forward Current 正向电流	I_F	200	mA
Peak Forward Surge Current 峰值正向浪涌电流	I_{FSM}	500@1S 1000@1mS 4000@1μS	mA
Reverse Voltage 反向电压	V_R	75	V
Peak Reverse Voltage 峰值反向电压	V_{RM}	100	V
Power dissipation 耗散功率	PD	500($T_a=25^{\circ}C$)	mW
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-65to+175 $^{\circ}C$	

■ Electrical Characteristics 电特性

($T_A=25^{\circ}C$ unless otherwise noted 如无特殊说明, 温度为 $25^{\circ}C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压 ($I_R=100\mu A$)	$V_{(BR)}$	100	—	V
Reverse Leakage Current 反向漏电流 ($V_R=20V$) ($V_R=75V$) ($V_R=20V, T_J=150^{\circ}C$)	I_R	—	25 5 50	nA μA μA
Forward Voltage 正向电压 ($I_F=10mA$)	V_F	—	1	V
Diode Capacitance 二极管电容 ($V_R=0V, f=1MHz$)	C_D	—	4	pF
Reverse Recovery Time 反向恢复时间	T_{rr}	—	4	nS

■ Typical Characteristic Curve 典型特性曲线

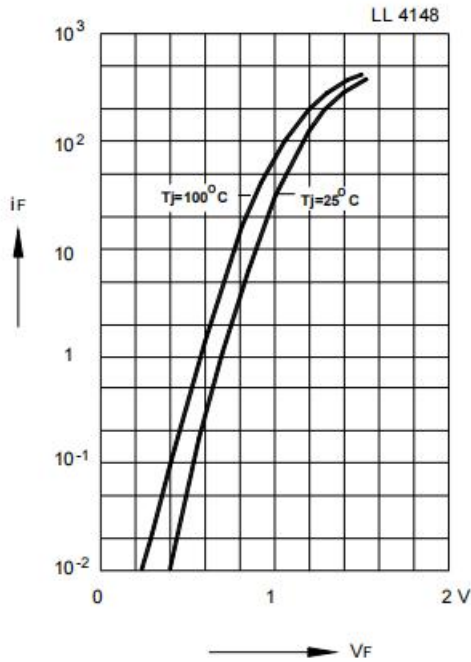


Figure 1: Forward Characteristics

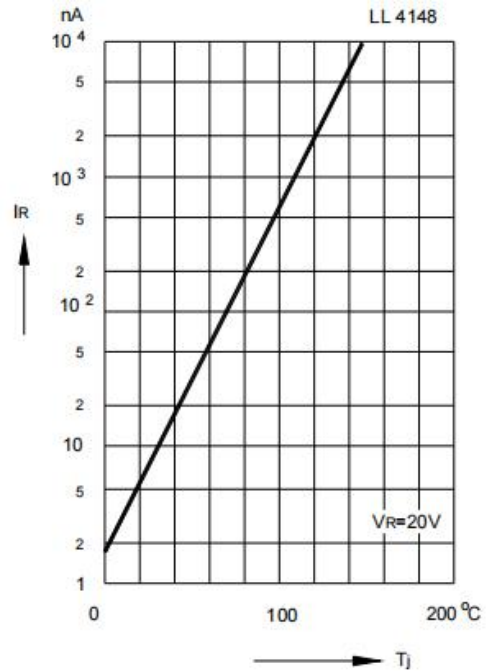


Figure 2: Leakage Current

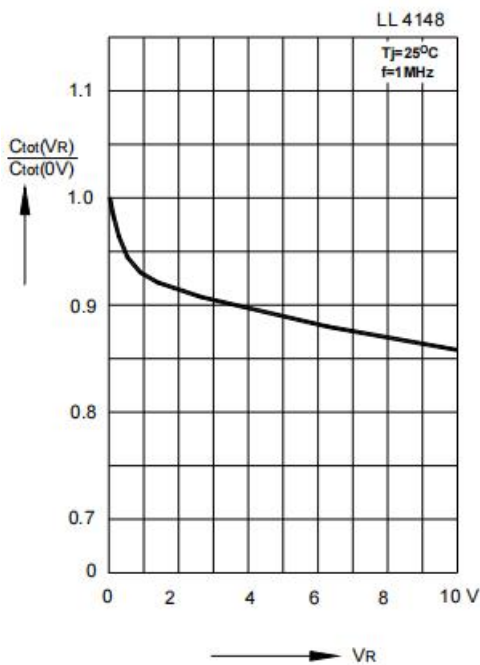


Figure 3: Capacitance Characteristics

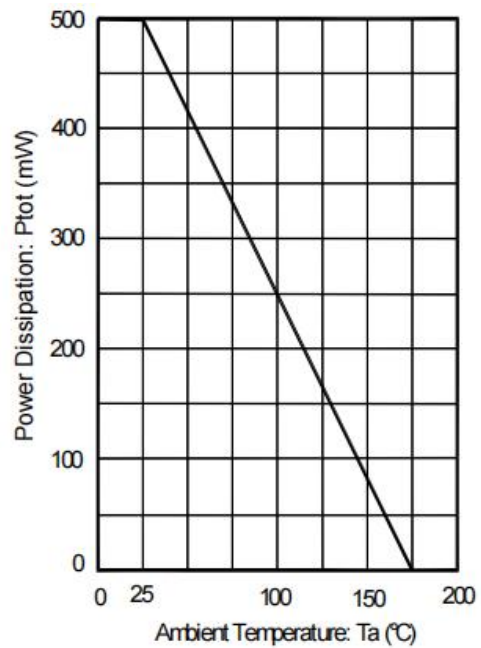
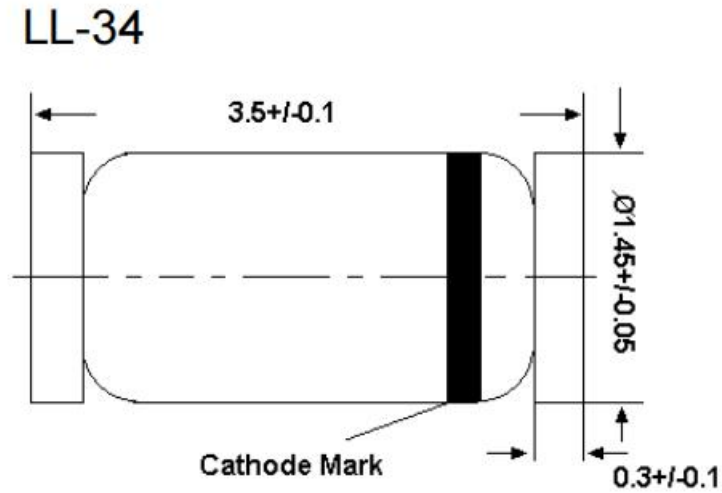


Figure 4: Power Derating Curve

■Dimension 外形封装尺寸



Glass case MiniMELF
Dimensions in mm